L Number	Hits	Search Text	DB	Time stamp
-	2	("6677613").PN.	USPAT; US-PGPUB;	2004/10/21 11:08
-	2	"20040036071"	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/10/21
	_		EPO; JPO; DERWENT; IBM_TDB	
-	1	"5463483".PN.	USPAT	2004/10/21 11:23
_	1	"5594569".PN.	USPAT	2004/10/21 11:23
-	1	"5856689".PN.	USPAT	2004/10/21
-	1	"5904514".PN.	USPAT	2004/10/21 11:25
-	1	"5998841".PN.	USPAT	2004/10/21 11:25
-	1	"6162654".PN.	USPAT	2004/10/21 11:26
-	1	"6208392".PN.	USPAT	2004/10/21 11:26
-	1	"6271543".PN.	USPAT	2004/10/21 11:29
-	704	@ad<=19990303 and (257/72).ccls.	USPAT; US-PGPUB; EPO; JPO;	2004/10/21 12:01
-	385	@ad<=19990303 and (257/79).ccls,.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/21 11:55
-	648	@ad<=19990303 and (257/40).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/10/21 11:56
-	91	@ad<=19990303 and (257/83).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/21 11:56
-	450	@ad<=19990303 and (257/88).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/21 11:56
_	261	@ad<=19990303 and 'liquid crystal display' and 'transistor' and 'light shielding layer' and 'pixel electrode'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/21 11:58
-	34	@ad<=19990303 and 'liquid crystal display' and 'transistor' and 'light shielding layer' and 'pixel electrode' and 'storage capacitance'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/21 14:13
-	1812	@ad<=19990303 and (345/87).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/21 12:02

-	537	@ad<=19990303 and (345/92).ccls.	USPAT;	2004/10/21
			US-PGPUB; EPO; JPO;	12:05
			DERWENT;	
	l .		IBM TDB	
-	998	@ad<=19990303 and (345/102-104).ccls.	USPĀT;	2004/10/21
,	-		US-PGPUB;	12:04
		,	EPO; JPO;	
			DERWENT; IBM TDB	
_	784	@ad<=19990303 and (345/94).ccls.	USPAT;	2004/10/21
-		(0.10, 5.1, 1.0025)	US-PGPUB;	13:11
	•		EPO; JPO;	
			DERWENT;	
		HC157400H PV	IBM_TDB	
_	1	"6157429".PN.	USPAT	2004/10/21 13:05
l <u> </u>	1	"6127998".PN.	USPAT	2004/10/21
	_		"	13:06
_	1	"5827755".PN.	USPAT	2004/10/21
Į		,		13:06 ,
-] 1	"5815223".PN.	USPAT	2004/10/21
_	1	 "5691794".PN.	USPAT	13:07 2004/10/21
_	ļ	3091794 .FN.	USPAI	13:09
_	1	"5591990".PN.	USPAT	2004/10/21
		·		13:10
-	1	"5200926".PN.	USPAT	2004/10/21
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-	1282	@ad<=19990303 and (349/42).ccls.	USPAT; US-PGPUB;	2004/10/21 13:12
			EPO; JPO;	13.12
			DERWENT;	
			IBM_TDB	i
-	1625	@ad<=19990303 and (349/139).ccls	USPAT;	2004/10/21
			US-PGPUB;	13:14
			EPO; JPO; DERWENT;	
		·	IBM TDB	
	1011	@ad<=19990303 and (349/138).ccls	USPAT;	2004/10/21
			US-PGPUB;	13:15
		·	EPO; JPO;	
			DERWENT; IBM TDB	
_	1360	@ad<=19990303 and (349/158).ccls	USPAT;	2004/10/21
		(0.10, 1.00, 0.00)	US-PGPUB;	13:17
			EPO; JPO;	
			DERWENT;	
_	130	 @ad<=19990303 and (349/145).ccls	IBM_TDB USPAT;	2004/10/21
-	130	eau\-19990000 and (349/140).0018	US-PGPUB;	13:27
			EPO; JPO;	10.27
			DERWENT;	
		0.44.10000000	IBM_TDB	0004/10/01
_	108	@ad<=19990303 and (368/30).ccls	USPAT; US-PGPUB;	2004/10/21
			EPO; JPO;	15.51
			DERWENT;	
			IBM_TDB	
-	3	• · · · · - · · · · · · · · · · · · · ·	USPAT;	2004/10/21
		device' and 'silicon substrate' and 'active matrix pixel'	US-PGPUB; EPO; JPO;	13:53
		accive macrix bixer	DERWENT;	
			IBM TDB	
-	14		USPAT;	2004/10/21
		substrate' and 'resin' and 'shielding	US-PGPUB;	13:54
	ŀ	layer' and 'pixel'	EPO; JPO;	
			DERWENT; IBM TDB	
L	<u> </u>	<u></u>	+ 	<u> </u>

_	3	<pre>@ad<=19990303 and 'silicon substrate' and 'transistor' and 'light shielding layer' and 'pixel electrode' and 'storage capacitance'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/21 14:56
-	79	@ad<=19990303 and 'dielectric' same 'SiO' same 'polyimide'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/21 14:58
-	45	@ad<=19990303 and 'dielectric' same 'SiO' with 'polyimide'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/21 15:15
-	74	@ad<=19990303 and 'dielectric' with 'SOG' with 'polyimide'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/21 15:05
-	6	@ad<=19990303 and 'dielectric' with 'SOG' with 'BCB'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/21 15:07
_	1	@ad<=19990303 and 'dielectric' same 'SOG' same 'P' adj1 'SiO'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/21 15:08
	5	@ad<=19990303 and 'dielectric' same 'P' adj1 'SiO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/21 15:09
	1	<pre>@ad<=19990303 and 'dielectric' same 'SiO' with 'BCB'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/21 15:16
-	14	<pre>@ad<=19990303 and 'dielectric' same 'SiO' with 'polyamide' .</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/22 09:20
-	1	<pre>@ad<=19990303 and 'dielectric' same 'PSG' with 'BPSG' with 'BCB'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/22 09:21
_		@ad<=19990303 and 'dielectric' same 'PSG' with 'BCB'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/22 09:21
_	61	@ad<=19990303 and 'dielectric' with 'PSG' with 'polyimide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/22 09:34
-	2	("6157429").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/22 09:34